

Index

a

- AAO. *see* anodic aluminum oxide (AAO)
- ABC MLD system 92
- mass gain from QCM measurements 92, 93
 - reaction sequence for growth of alumina–siloxane film using 100
 - TMA diffusion 92
 - use of
 - heterobifunctional precursor 96–99
 - homotrifunctional precursor 93–96
- acid/base catalysis during silica formation 73
- activation barriers, calculation 10–12
- adsorption energy 15, 17
- advanced photonic crystals
- multilayer fabrication steps 360–366
- advanced photonic crystals, multilayer fabrication. *see also* NCP inverse opal
- ALD tool 360
 - conformal multilayer approach 361
 - photoluminescence spectrum of Mn ion 361
 - SEM image, multilayered inverse opal 361
- aerogels 240–242
- filaments 241
- alanes 404
- ALD Al₂O₃-coated ZnO nanorods
- TEM images 262
- ALD Al₂O₃-coated ZnO NWs 261
- ALD-based optics, in soft X-ray spectroscopy 380
- ALD, characteristics 255, 261
- ALD coating technology 382
- ALD Cu₂S
- film on silicon trench structure 232
 - infiltration depth 244
- ALD nucleation mechanisms 290
- ALD of thin films, challenges 401
- Al-doped ZnO layers 114
- ALD precursors 42
- ALD reactor 34
- TFS 200 141
 - triode configuration 140, 141
- ALD shell 265
- ALD TiO₂ inverse opals
- cross sections, SEM images 238
- ALD ZnO
- film 265
 - growth, in AAO nanopores 235
 - on NWs/tubes 265–267
- ALE. *see* atomic layer epitaxy (ALE)
- ALE of III–V semiconductors 410
- Al–H bond 404
- alkoxysilanols 74
- alkyl halide condensation 75, 76
- alkyl halide elimination 73
- reaction approach in ALD 74
- alkyl phosphines 403
- alkylsiloxane 385
- alkylsilylamines 50
- Al₂O₃ ALD cycles 289, 290
- Al₂O₃ ALD layers 381
- Al₂O₃ ALD process 239
- Al₂O₃ film 36
- Al₂O₃/W interface 381
- Al₂O₃/ZrO₂ nanolaminate 118, 121
- gas diffusion barrier 118, 119
 - *I–I–V* characteristics between Al₂O₃ and 120
 - x-ray photoemission spectroscopy 119
- alucone 119
- based on TMA and EG 85, 86
- alumina 66, 67, 69, 141, 231, 261, 265, 274, 282, 380, 381, 387–389
- biocompatibility of 317

- alumina-coated titania nanoparticles. *see also* nanoparticles
 - TEM image 252
 - alumina–siloxane MLD film 100
 - FTIR difference spectra 100
 - aluminium, EDAX elemental maps 239
 - aluminosilicates 69
 - aluminum ALD, with hydrogen plasma and TMA 403
 - aluminum films 404
 - aluminum oxide 416
 - atomic layer deposition
 - idealized reaction scheme for 274
 - reaction scheme for 274
 - amidinates 43, 46, 403, 406
 - 3-aminopropyltriethoxysilane 74
 - analytical characterization techniques, to evaluate ALD coatings 228
 - anionic polyelectrolyte (poly(sodium 4-styrenesulfonate)) 330
 - anodic aluminum oxide (AAO) 34, 212, 231, 234–237, 319
 - SEM image 234
 - Zn concentration, cross-sectional EDAX images 235
 - antimony films 405
 - apoferritin 304
 - aqueous sol–gel 61
 - area-selective ALD schemes 211
 - area-selective atomic layer deposition 193–195
 - area-selective CVD (AS-CVD) 203
 - ArF excimer laser 162
 - Arsine 410
 - AS-ALD applications 215, 216, 218
 - current challenges 216–218
 - patterning method 206
 - as-synthesized GaN nanowires
 - energy diagrams 257
 - atomic layer deposition (ALD), simulations
 - *ab initio* MD 13
 - BOMD approach 13
 - CPMD method 13
 - adsorption reactions 14, 15
 - gas-phase reactions 14
 - ligand exchange reactions 15, 16
 - mechanism with DFT
 - Al₂O₃ using TMA and water 16–20
 - half-reactions 16, 18
 - reaction energies 19
 - clusters used to model reactive sites on Al₂O₃ surface 17
 - key challenges 13
 - quantum simulation approach 13
 - surface reactions 14–16
 - atomic layer epitaxy (ALE) 83, 133, 134, 256, 257, 358, 409
 - of GaAs using H radicals 133
 - atomistic simulations 3
 - Auger elemental maps 208
 - Au(III) complexes 403
 - Au nanoparticles 255
- b**
- band gap semiconductors 260
 - BET surface analysis 286
 - bilayer NW system 261
 - binary compounds 406
 - borides 412
 - carbides 410, 411
 - compounds with oxoanions 413, 414
 - halides 412, 413
 - nitrides 408, 409
 - other III–V compounds 410
 - oxides 406–408
 - silicides 412
 - binary semiconductor nanowires
 - VLS growth 256
 - biocompatibility. *see* biocompatible coatings
 - biocompatible coatings 317
 - alumina 317
 - hydroxyapatite 318
 - Pt-, TiO₂-, or ZnO-coated porous alumina 318, 319
 - tin-coated cotton fabrics 319, 320
 - titania 318
 - biological nanostructures 109
 - biomineralization 308
 - biomineralized structures 316, 317
 - bis(dimethylamino)dimethylsilane 100
 - block copolymers 282
 - Boltzmann constant 12, 229
 - Born–Oppenheimer (BOMD) method 13
 - bottom-up techniques
 - vapor–liquid–solid (VLS)/solution growth 255
 - Bragg diffractions 345, 346
 - properties of opals 348
 - Bragg–Snell relationship 346, 347
 - bulk heterojunction 123
 - P3HT:PCBM 123, 124
 - 1,4-butanol 86
- c**
- carbon aerogel
 - TEM images 243
 - carbon nanotube (CNT) 307, 327, 328

- ALD coating of other sp^2 -bonded carbon materials 338, 339
 - atomic layer deposition on 331–337
 - coated with V_2O_4 , TEM images 336
 - coating of large quantity by ALD 337
 - fluidized bed reactor apparatus 338
 - rotary reactor 339
 - decoration, and coating 329
 - by gas-phase techniques 330, 331
 - preformed nanobuilding blocks, attachment of 330
 - *in situ* coating 329, 330
 - HNO_3 -treated MWCNTs with 333
 - material combinations, and synthesis procedures 327
 - purification 328, 329
 - Ru-coated MWCNT array 333
 - single-wall CNTs 329, 332–335
 - ethanol-dispersed, TEM image of Al_2O_3 ALD on 334
 - noncovalent coating 334
 - NO_2 /TMA functionalized, ALD coating behavior 332
 - SnO_2 -coated 336
 - surface functionalization 328, 329
 - TEM image of untreated MWCNTs 335
 - carboxylic acids 62, 67–69, 75, 86, 91, 99, 105, 328, 335, 338, 402
 - Car-Parrinello (CPMD) method 13
 - Ca sensors 118
 - CCSD(T) coupled cluster method 12
 - cellulose cotton fibers 282
 - transmission electron microscopy (TEM) image 272
 - cesium carbonate 123
 - chalcogenide thin films 50
 - chemical beam epitaxy (CBE) 255
 - chemical vapor deposition (CVD) 24, 26, 195, 255, 354
 - chemical vapor deposition 14
 - in chemical vapor deposition 26
 - contribution to MLD growth 87
 - precursor diffusion lead to 86
 - reactor 26
 - from tin hydride (SnH_4) in nitrogen 331
 - chirped mirrors 380
 - CMOS (complementary metal oxide semiconductor) devices 146
 - CNT. *see* carbon nanotube (CNT)
 - coaxial cables 331
 - cold plasmas 134, 135
 - collisional plasma sheath 135
 - colloid chemical methods 257
 - comb-like 2D hollow nanostructure 261
 - computational quantum mechanical methods 8
 - contact angle 196
 - copper diffusion barrier 243
 - copper film 402
 - copper sulfide (Cu_2S) film 232
 - cross-sectional SEM images 232
 - core-shell NWs 263
 - crystalline ZnO 180
 - Cu diffusion barriers 133
 - Cu nanoparticles 259
 - chain formation mechanism 259
 - CVD. *see* chemical vapor deposition (CVD)
 - cyclic siloxanes 100
 - cyclopentadienyl compounds 47, 48, 406, 412
- d**
- decamethylcyclopentasiloxane 100
 - density functional-based quantum simulations 6–8
 - density functional theory (DFT) 5
 - *ab initio* study based on 199
 - of Al_2O_3 ALD on self-assembled monolayers with 285
 - calculations indicate 97
 - DFT-based MD 13
 - drawback 7
 - for reaction of trimethylaluminum (TMA) on 199
 - DEZ exposure 236
 - time 240
 - DEZ/ H_2O forms ZnO layers 114
 - DFT energy functionals 7
 - diblock copolymers 212
 - 1,3-dichlorotetramethyldisiloxane 100
 - dielectric ALD nanolaminates 380
 - diethylzinc (DEZ) 86, 279, 310
 - diethylzinc, for ZnO ALD 236
 - diffractive optical elements 381–383
 - diffusion-limited regime 228, 230
 - diisopropyl-isopropoxy-silane (DIPS) 102
 - β -diketone 403
 - dimethylmethoxychlorosilane (DMMCS) 100–102
 - 2,2-dimethylpropionato silver(I) triphenylphosphine 403
 - diphenylalanine 305, 306
 - DIPS/ H_2O /TMA sequence 102
 - DNA functionalization, for nanotube electronics 307
 - DRAM. *see* dynamic random access memory (DRAM)
 - dye-sensitized solar cells (DSSCs) 304, 306

- photoelectrode in 258
 - dynamic random access memory (DRAM) 24, 162–168
 - Cp-based precursors, for DRAM industry 146
 - CVD W plug and lines used in 186
 - for decreasing stray capacitance 187
 - memory cell-to-periphery region of 186
- e**
- E. coli* 319
 - EDAX measurements 239, 240
 - electron cyclotron resonance (ECR) plasmas 141
 - electron–electron repulsions 7
 - electron energy 135
 - electron impact collisions 137
 - electron–nuclear attractions 7
 - electron temperature 135
 - electropositive metals 403, 404, 416
 - electropositive plasma 135
 - electrospun polymer fibers
 - tube-in-tube structure consisting 262
 - electrospun polyvinylpyrrolidone 283
 - electrospun synthetic polymer nanofibers 283
 - element-specific analytical technique 231
 - encapsulation
 - external quantum efficiency η_{ext} vs. current density 122
 - inverted cell 123
 - nanolaminate, identified as important for 384
 - of organic light emitting diodes 119–123, 277, 384
 - of organic solar cells 123–125
 - thin film 383–385
 - energy-dispersive X-ray mapping 282
 - EPMA mapping 34
 - ethanolamine (EA) 86
 - ethylene glycol (EG) 85, 87
 - ethylene tetrafluoroethylene (ETFE) 276
 - exchange correlation (XC) functionals 5
 - ex situ* x-ray reflectivity (XRR) 87, 100, 380, 381
- f**
- fabrication technology 161, 258
 - for Au@SiO₂ and Au@Ga₂O₃ systems 258
 - 3D PCs fabricated with various processes 352
 - 3D stacking trends in semiconductor chip 162
 - SAM patterns by using photolithography 209
 - Fabry–Perot bandpass filter 378
 - transmittance spectrum 378
 - fcc lattice 352
 - ferritin 304
 - ferroelectric RAM (FeRAM) 174–177
 - fibroblast cells 318
 - field effect transistor (FET) devices 258
 - omega-shaped gate 258
 - film thickness 33, 161
 - film transistors (TFTs) 116
 - finite and extended quantum simulations 8, 9
 - finite-difference time-domain (FDTD) 349, 357
 - flash memory 162, 168–172
 - FlexAL* and *OpAL* reactors 141
 - flexible electronic devices, ALD process development 276
 - fluorine 45, 381, 408
 - focused ion beam (FIB) 231
 - focused ion beam scanning electron micrograph (FIBSEM) 382
 - nanostructure coated with alumina/titania multilayer 383
 - Fourier expansions 9
 - Fourier transform infrared (FTIR), difference spectra 231
 - after TMA and GL exposures during AB alucone MLD 94
 - after TMA, EA, and MA exposures during ABC MLD 91
 - after TMA, H₂O, and CI exposures during ABC MLD 98
 - after TMA, H₂O, DMMCS, and H₂O exposures during ABCD MLD 101
 - *in situ* measurements of surface hydroxyl loss 236
 - full photonic band gap (FPBG) 349, 350, 353–357, 359
 - full-width at half-maximum (FWHM) 379
- g**
- Ga–As bonds 8
 - gallium acetylacetonate 330
 - GaN NWs, coated with ALD Al₂O₃, 257
 - gas diffusion barrier 103, 112, 113
 - thin film 117–119
 - germane (GeH₄) 354
 - glancing angle deposition (GLAD) 350
 - gold 403
 - Gordon method 229
 - Gordon's equation 35

grazing angle 381
 grazing angle X-ray diffraction (GIXRD) 381
 guided-mode resonance (GMR)-type Wood's anomalies 382

h

hafnium oxide 34
 hafnium tetra-tert-butoxide (HTB) 305
 halogenated precursors 245
 heat-resistant substrates 266
 heterobifunctional precursor 96–99
 hexafluoroisopropyl alcohol (HFA-PNB) 202
 hexagonal close-packed arrangement 234
 hexamethylcyclotrisiloxane 100
 hexamethyldisilazane (HMDS) 201, 212
 HfO₂ coating 20, 48, 65, 110, 179, 182, 277, 305
 HfO₂ nanodots 305
 high aspect ratio structures
 – AAO membranes 244
 – ALD coatings, characterization methods 230–232
 – ALD, examples of 232–242
 – analytical method 229
 – aspect ratio of 10 232–234
 – aspect ratio of 100 234–238
 – aspect ratio of 1000 and beyond 238–242
 – coatings on 227, 228
 – infiltration 245
 – models and analysis 228–230
 – Monte Carlo simulations 229, 230
 – nonideal behavior during ALD 242–245
 homobifunctional precursors 86
 HOMO–LUMO gaps 10
 homotrifunctional precursor 93–96
 hopping coefficient 230
 horizontal CVD reactor with tilted substrate 27
 human adipose-derived adult stem cells (hADSCs) 319
 – viability images of 320
 hybrid inorganic–polymer multilayers 384
 hybrid organic/inorganic electronic devices 278
 hybrid organic–inorganic MLD 84
 hybrid organic/metal oxide network polymer 279
 hybrid polymer calcination 280
 hydrophobic polypropylene fibers 278
 hydroquinone 86
 hygroscopic Cs₂CO₃ interlayers 124
 hyperbranched ZnO nanostructures
 – fabrication 267

i

indium tin oxide (ITO) 104, 123, 407
 inductively coupled plasma (ICP) 139
 – RF-driven 141
in situ infrared transmission analysis
 – polymer/reactant interactions 283
 inorganic polymerization 61, 76
 inorganic precursors, for ALD 44
 – coordinated through other inorganic elements 46, 47
 – elemental precursors 44
 – halides 44
 – nitrogen-coordinated precursors 46
 – oxygen-coordinated compounds 44–46
in situ ellipsometry 382
in situ FTIR spectroscopy, revealing catalytic pathway 74
in situ study of mechanisms in ALD 70–72
 interference optics 377
 inverse shell opals 349–352. *see also* NCP
 inverse opal; synthetic opals
 – Bragg diffraction properties 348
 – electric field effects 368, 369
 – experimental steps to fabricate 347
 – large-pore and non-close-packed 352, 353
 – schematic of opal formation 369
 – typical growth and processing flow path 365, 366
 ion bombardment 135, 136, 141, 151, 152
 ion energies 135, 141
 – distribution 136
 ionic bonding 196
 ionization degree 135
 ionized PVD (I-PVD) 26
 ion–surface interactions 136
 – during plasma processes 137
 isopropyl alcohol 69, 278
 isothermal heating evaporation-induced self-assembly (IHEISA) technique 352

j

J-aggregates 310

k

kinetic isotope effect (KIE) 12
 Kirkendall effect 261, 262, 265
 Knudsen diffusion 229, 243
 – of ALD precursors 229
 Kodak's process 115, 116
 Kronig–Penny model 346
k-value, of oxides 151

I

Langmuir adsorption 228, 229
 Lewis acid 15, 17, 68, 73–75, 103, 285, 291
 Lewis base 15, 17, 103
 light emitting diodes (LEDs) 378
 Li ion batteries 404
 liquid crystal (LC) 366
 lithography etching 23, 255
 logic devices, ALD for 180. *see also* MISFET
 – back end of line process 185–187
 – interconnect stack up to MT8 185
 – memory cell-to-periphery region of DRAMs 186
 – front end of line process 180–184
 low-temperature ALD (LT-ALD) 109, 111
 – challenges 110
 LP inverse opal 367

m

magnetic RAM (MRAM) 174, 178
 maleic anhydride (MA) 89
 many body perturbation theory (MBPT) 6
 Maxwellian/Druyvesteyn-like energy distribution 135
 memory devices, ALD layers for 162
 – dynamic random access memory (DRAM) 162–168
 – ferroelectric RAM (FeRAM) 174–177
 – flash memory 162, 168–172
 – magnetic RAM (MRAM) 174, 178
 – phase change RAM (PCRAM) 162, 163, 172–174
 – resistive RAM (ReRAM) 174, 178, 179
 – three-dimensional stacked memories 179, 180
 mercaptoundecanol (MOU) 197
 metal alkoxides 49, 65, 66, 68, 69, 73, 75
 – beta-elimination reaction 76
 metal alkyls 105
 metal-catalyzed CVD process 255
 metal halides 44, 65, 67, 73, 75, 405
 metallic nanolaminates 380
 metallic precursors, for ALD 42–44
 metallic tungsten 276
 metal nanoparticles
 – ALD coating on 253
 – decorated nanotubes 265
 – effective protection for 252
 metal-organic CVD (MOCVD) 47, 176, 256, 351, 358, 409, 410
 metal oxide ALD deposition, from water/hydrogen peroxide 70
 metal oxide deposition, under nonaqueous conditions 67
 – alkyl halide elimination 67, 68
 – ester elimination 68, 69
 – ether elimination 68
 metal oxide formation, via hydrolytic routes 64
 – reaction with
 – metal alkoxide 65, 66
 – metal halides 64, 65
 – organometallic compounds 66
 metal oxides 279
 – nanoparticles 69
 – TFTs 116
 – thin films, by ALD 64
 metal precursor 402
 1-methoxy-4-(2'-ethyl-hexyloxy)-2,5-phenylene vinylene (MEH-PPV) 278
 microcontact printing (μ CP) 205
 microelectromechanical systems (MEMS) 23, 110, 233
 – FIB-cut cantilever, SEM images 233
 microelectronics device fabrication 215
 microwave plasmas 141
 MIM capacitors 146
 – using AS-ALD of Ru 215
 minimum energy path (MEP) 11
 MISFET
 – alternative approach for fabrication 183
 – capping layer approach 183
 – channel delay 185
 – conformal film growth properties of ALD 182
 – electrical roles for fabrication, and electrical operation of 184
 – Fermi-level pinning effects 183
 – gate-first and last process, with high- k gate dielectrics 181
 – logic MISFET fabrication process 180
 – n- and p-type MISFETs 180
 – silicidation of poly-Si gate and 183
 MLD. *see* molecular layer deposition (MLD)
 MOCVD. *see* metal-organic CVD (MOCVD)
 molecular dynamics (MD)
 – *Ab initio* MD 13
 – potentials not capable of 4
 molecular layer deposition (MLD) 44, 72
 – combination of ALD and 119
 – explored by several groups to produce surface polymers 285
 – of hybrid organic–inorganic films 83
 – prospects for 103–105
 – sequences 285
 – three-step reaction sequence
 – FTIR difference spectra 91
 – using TMA, EA, and MA 90

- using trimethylaluminum and ethylene glycol
- in AB process 87–89
- M–O–M bonds 63
- formation 70
- monodisperse silica nanospheres 237
- Monte Carlo simulations 149, 229, 230
- of ALD infiltration process 235
- to analyze ALD in nanopores 229
- quantitative agreement with 235
- surface recombination of radicals during plasma ALD 150
- Moore's law 161
- Morpho peleides* 312
- multilayer ALD coatings 382
- multiple pulse vapor infiltration (MPI) 279
- n**
- nanobowls
- by ALD on polystyrene spheres 254
- nanoelectromechanical systems (NEMS) 23
- nanolaminates 84, 113, 117, 118, 120, 122, 124, 379, 381, 383–388, 391–393
- complex nanostructures, importance of 394, 395
- copper electroplating applications 392, 393
- effective encapsulation materials, for PVCs and OLEDs 384
- electronics, applications in 386, 387
- dielectric properties 387–391
- memories, applications for 391, 392
- optical applications 377–383
- solid oxide fuel cells 393
- Ta₂O₅–Al₂O₃ nanolaminate 383
- TiO₂/Al₂O₃ nanolaminates 380
- TiO₂/NiO ALD nanolaminates 380
- TiO₂/ZnO nanolaminates 380
- nanomaterials 63
- ALD-coated 231, 395
- synthesis 63
- with tunable structure 228
- nanoparticles
- ALD on 251–254
- alumina-coated titania 252
- amorphous TiO₂ coating on magnetic 253
- atomic layer deposition on 251–254
- Au nanoparticles 255
- coating 251
- of colloidal ZnO 266
- of MWCNTs with SnO₂ 331
- colloids/monodispersed 62
- conventional titania 306
- Cu nanoparticles 259
- doped oxide 63
- metal 245, 252, 255, 328
- photodeposition of silver 281
- polymer, ALD on 253
- synthesis
- of metal oxide 69
- of oxide 63
- titania 69
- uncoated/alumina-coated TiO₂ 251
- nanopeapods
- ALD-assisted formation 258, 259
- nanoribbons 306
- nanotemplates 212, 213
- nanotubes
- ALD ZnO as seed layer for growth of hyperbranch 265–267
- fabrication process using AS-ALD 213
- formation, by photocatalytic effect 260
- TiO₂, ZrO₂, and ZnO nanotube fabrication 212
- nanowires
- ALD growth process 255
- ALD ZnO as seed layer for growth of 265–267
- atomic layer epitaxy on 256, 257
- coatings 251
- interface reaction, with ALD shell 261–265
- MgO–Al₂O₃ 265
- ZnO–Al₂O₃ 261, 262
- ZnO–TiO₂ 264, 265
- semiconductor, photocorrosion capped by ALD shell 260, 261
- surface passivation, ALD on semiconductor 257, 258
- vapor–liquid–solid growth by ALD 254–256
- natural fibers 307
- cellulose fibers from paper 310
- collagen 308
- cotton fibers 310, 311
- DNA 307
- sea mouse bristles 311, 312
- spider silk 308–310
- natural opal gemstone 346
- natural polymer fibers 271, 281
- NCP inverse opal 357, 359
- double infiltration techniques 364
- holographic lithography combined with 364
- holographic template inversion
- and replication protocols 365
- modified NCP fabrication scheme 361
- sacrificial layer techniques, for fabrication 362

- static tunability vs. backfilling in sacrificial layer 364
 - template-patterned sacrificial layer ALD for 362
 - N–H bonding 203
 - NHSG conditions applied to ALD 70
 - nitridation 143, 151, 358
 - nonaqueous sol–gel 62, 63
 - nanomaterials, synthesis of 63
 - nonmetal elements 404, 405
 - nonmetal precursors 402
 - for ALD 49
 - oxygen sources 49, 50
 - reducing agents 49
 - S, Se, and Te, elemental metal precursors 50
 - N₂- or NH₃-based plasmas 151
 - novel PC structures 382
 - nucleation 415, 416
 - of ALD 290, 338
 - delay 149
 - properties of ALD affecting 416
 - TiN ALD layer 275
 - nylon 6 289
- o**
- octadecanethiol (ODT) 197
 - 1-octadecene 204, 210
 - octadecyltrichlorosilane (ODTS) 195, 201, 204, 209, 212, 213, 216, 304, 305
 - ODTS SAM
 - coated on SiO₂ surface 196
 - formed only on PR-free regions of substrate 209
 - structure 196
 - ommatidia 314
 - opal structures, inversion 353–357
 - ALD technique 357–359
 - processes and capabilities 366
 - with FPBGs 354
 - functional materials, infiltrated into 359
 - infiltration techniques 357
 - inverse Si opal, reflection spectrum of 354
 - inverse ZnS:Mn opals 358
 - luminescent inverse opals structures 360
 - micromolding in silica inverse opals (MISO) 356
 - process steps 356
 - Sb₂S₃ inverted opal 355
 - selective chemical etching 356
 - techniques 354
 - using germane (GeH₄) 354
 - ZnO inverse opals, optical properties of 360
 - optical applications, of ALD multilayers 378
 - optical emission spectroscopy (OES) 137
 - optical filters 382
 - organic electronics 119
 - organic–inorganic alloys 84
 - organic–inorganic bilayer structures 284
 - organic–inorganic hybrid nanolaminates 384
 - organic–inorganic polymers 99
 - organic–inorganic superlattices 385
 - organic LEDs 404
 - organic light emitting devices 119–123
 - encapsulated, *I*–*V* characteristics 122
 - organic light emitting diodes 277, 384
 - encapsulation 119–122
 - organic photovoltaic cells (OPVs) 119, 277
 - organic solar cells (OSCs) 123
 - encapsulation 123–125
 - organic thin film transistors (OTFTs) 277
 - organoaluminum compounds 291
 - organometallic ALD precursors 47
 - cyclopentadienyl-type compounds 47–49
 - metal alkyls 47
 - for preparation of bismuth- and lead-containing oxide thin films 49
 - organosilicon SAMs 197
 - oxo–metal bonds 63
- p**
- palladium(II) hexafluoroacetylacetonate (Pd^{II}(hfac)₂) 114, 115
 - Papilio blumei* 313
 - patterned biomaterials 312
 - butterfly wings 312–314
 - fly eyes 314, 315
 - legumes 315
 - water strider legs 315, 316
 - model states 315
 - patterning 205
 - microcontact printing 205–207
 - nanotemplating 212, 213
 - photolithography 207, 209–212
 - scanning probe microscopy 213, 214
 - surface modification without patterning 205
 - PAZO dye 315
 - PBGs. *see* photonic band gaps (PBGs)
 - PEALD. *see* plasma-enhanced ALD (PEALD)
 - peptide assemblies 305, 306
 - PES. *see* potential energy surface (PES)
 - phase change RAM (PCRAM) 162, 163, 172–174
 - phase change random access memories (PCRAM) 405

- phosphoric acid 332
- photocatalytic lithography 210
- photolithography-assisted patterning with polymer 211
- photoluminescence 317, 382
- photonic band gaps (PBGs) 281, 346, 348, 352, 354, 357, 360, 363, 370, 382
- photonic crystal (PC) 254, 280, 350, 359, 360, 382
 - concept 345
- photoresist 162, 201, 209, 280
- P3HT/[6,6]-phenyl-C₆₁-butyric acid methyl ester (PCBM) heterojunction solar cells 277
- physical vapor deposition (PVD) 24–26, 28, 131, 261, 271, 272, 417
 - dependence of step coverage on 26
- pitch 162
- plane wave expansion (PWE) 349
- plasma ALD 131, 132, 136
 - ability to synthesize materials 146
 - challenges 143–153
 - configurations 139–142
 - densities of plasma species
 - in O₂ plasma 139
 - equipment 141
 - configuration 141
 - electron cyclotron resonance (ECR) plasmas 141
 - *FlexAL* and *OpAL* reactors 141
 - microwave plasmas 141
 - RF-driven inductively-coupled plasmas 141
 - ion–surface interactions during plasma processes 137
 - merits of 142, 143
 - optical emission spectrum 138
 - properties of plasma step 136
 - reactor layout 134
 - recombination loss probabilities for materials 138
 - and thermal ALD, key differences between 137
 - of TiO₂ films 145
 - for various material systems 143
- plasma, defined 134
- plasma-enhanced ALD (PEALD) 114, 115, 131, 132, 216, 388, 389, 393
 - degradation of ODTS SAMs 216
 - films 173
 - used to deposit CoSi₂ films 412
 - using TMA, and a remote O₂ plasma 277
- plasma-enhanced chemical vapor deposition (PECVD) 124, 140
- plasma-induced damage 151
- plasma operating conditions 136
- plasma potential 135
- plasma radicals 135, 140–142, 149
- polarized reflectance spectra 382
 - of tunable GMR filter 382
- polyamide 83, 119, 290
- polyamide 6 (PA-6) 274, 276, 289
- polyamide nylon 6 290
- polycarbonate (PC) nanotemplate 212
- polydimethylsiloxane (PDMS) 99, 100, 205–207, 215
- poly(ether ether ketone) (PEEK) 276
- polyethylene (PE) 276
- polyethylene naphthalate (PEN) 276
- polyethylene terephthalate (PET) 276
- polyferrocenylsilane (PFS) 368
- poly(3-hexylthiophene) (P3HT) 277
- polyhydroxystyrene (PHOST) 202
- polyimide (PI) 276
- polymer calcination 283
- polymer deactivator, for AS-ALD 202
- polymer/inorganic interface 272
- poly(methyl methacrylate) (PMMA) 201–203, 211, 214, 216, 276, 277, 279
- polypropylene 276
 - differential infrared transmission data 287
 - TEM micrographs 287
- polypropylene (PP) fiber matrix 271
- polystyrene (PS) 212, 276
 - closely packed monolayers 253, 267
- polystyrene-*block*-poly(2-vinylpyridine) (PS-*b*-P2VP) copolymer 282
- polytetrafluoroethylene (PTFE) 276
- polyurethane 119
- polyvinyl alcohol 288
 - Al₂O₃ ALD, infrared data 288
 - Al₂O₃ ALD, TEM images 288
- polyvinyl chloride (PVC) 276
- polyvinyl phenol (PVP) 277
- polyvinylpyrrolidone (PVP) 202, 203, 283
- potential energy surface (PES) 10–12, 17
 - for first half-reaction of TMA+ an OH site on Al₂O₃ surface 18
- power conversion efficiency (PCE) 124
- precursor partial pressure, in ALD 37
- pristine graphene 338
- protective coatings, for sensor systems 110
- protein-based nanostructures 302
 - apoferritin 304
 - ferritin 304
 - S-layers 304, 305
 - tobacco mosaic virus (TMV) 302–304

- PR (AZ4330) patterning by photolithography 209
- pseudo-PBGs (PPBGs) 351, 354
- pseudopotentials 9
- pulsed laser deposition 116
- pulsed metal-organic CVD (MOCVD) process 256
- pulsed vapor infiltration (PVI) 279
- PVA fiber matrix 289
- PVD. *see* physical vapor deposition (PVD)
- pyridine catalyst 114, 407
- q**
- quadrupole mass spectrometry (QMS) 231, 239, 402
- crystals 286
- quantum dot film 231
- quantum simulations 4
- calculation of properties using 10
 - finite and extended 8, 9
- quarter-wave optical thicknesses 378
- quartz crystal microbalance (QCM) 71, 231, 402
- quartz crystal microgravimetry 276
- quasineutrality 134
- quaternary compounds studied, in ALD 414, 415
- r**
- radical flux 149
- rates of reaction, calculation 12, 13
- refractive index 366, 378, 379
- of an Al₂O₃/TiO₂ composite 380
 - linear dependence of nanolaminate 379
- resistive RAM (ReRAM) 174, 178, 179
- resistivity of TaN films 147, 148
- deposited using Ta[N(CH₃)₂]₅ as a precursor 147
- retarding field energy analyzer (RFEA) 136
- RF-driven inductively-coupled plasmas 141
- Rh films 212
- ring-opening reaction 86, 91, 96
- roll-to-roll ALD processes 116
- roll-to-roll production environment 117
- Rutherford backscattering analysis 34
- Rutherford backscattering spectroscopy (RBS) 231
- r* values, of oxygen radicals 151
- s**
- sacrificial layers 162
- SAMs. *see* self-assembled monolayers (SAMs)
- Sb₂S₃
- conformal heteroepitaxial deposition 256
 - photonic band diagram and reflectance spectra 355
 - SEM image of Sb₂S₃ wires 255
 - VLS growth of binary semiconductor NWs Sb₂S₃ 255
- scanning electron microscopy (SEM) 231
- AAO membrane surface showing hexagonal arrangement 234
 - arrangement of silica beads 346
 - cross sections
 - of ALD TiO₂ inverse opals 238
 - SEM images of ALD Cu₂S film 232
 - SEM images of FIB-cut MEMS cantilever coated with 233
 - through completely backfilled structure 362
 - fabricated
 - RCAT DRAM cell 164
 - S-RCAT DRAM cell 164
 - of FeRAM cell structure 177
 - fractured frustule after TiO₂ coating 316
 - heavily sintered synthetic silica opal 353
 - of interconnect stack up to MT8 185
 - micrographs of ACCs consisting of titania/silica 214
 - multilayered inverse opal 361
 - MWCNT array 333
 - omega-shaped gate ZnO nanowire field 257
 - silica aerogel vs. ZnO ALD cycles 241
- Schrödinger equation 5
- secondary ion mass spectrometry (SIMS) 231
- self-assembled monolayers (SAMs) 195–197, 199–201, 284
- patterning by using SPM 215
- self-limiting binary reaction 272
- sequence 272
- self-limiting reactions, for MLDgrowth
- using two homobifunctional reactants 84
- SEM. *see* scanning electron microscopy (SEM)
- semiconductor devices 161
- semiconductor nanowires
- coating single crystals 256
- semiconductor nanowires (NWs) 254
- Si–Cl/Si–OR, condensation 73
- silanols 102
- silica aerogel
- vs. ZnO ALD cycle, SEM images 241
- silica deposition 72
- silica gel 238–240
- ALD Al₂O₃ infiltration measurements vs. TMA exposure 239
- silica-rich nonstoichiometric silicates 74

- silicon 69, 405
 - silicon trenches 232
 - silver 403
 - simulated body fluid (SBF) 318
 - Si precursor 75
 - Si wafer surface 305
 - S-layers 304
 - sodium dodecyl sulfate (SDS) 329
 - soft materials
 - ALD for
 - bulk modification of natural and synthetic polymers 279, 280
 - polymer sacrificial templating 280–283
 - polymers for passivation, encapsulation, and surface modification 274–279
 - Al₂O₃ ALD
 - mechanisms on PP, PVA, and PA-6, 290, 291
 - on polyamide 6, 289, 290
 - on polypropylene 286–288
 - on polyvinyl alcohol 288, 289
 - atomic layer deposition on 271–274
 - patterned and planar SAMs and surface oligomers
 - ALD nucleation on 283–285
 - representative polymer materials
 - Al₂O₃ ALD reactions on 286–291
 - solar cells. *see also* organic solar cells (OSCs)
 - development 257
 - dye sensitized 306
 - grown on plastic substrates 117
 - sol–gel chemistry 61, 62
 - sol–gel in solution 61
 - and in ALD, differences between 71
 - sol–gel technology 76
 - solid oxide fuel cells (SOFCs) 215, 393
 - solid-state reaction, of ZnO–TiO₂ core–shell NWs 262
 - solution-based processes 271
 - spinel MgAl₂O₄ nanotubes
 - formation 266
 - sputtering 116, 133, 161, 173, 183, 185, 186, 261, 262, 264, 331
 - Staphylococcus aureus* 319
 - step coverage models, in ALD 28
 - experimental verifications 34–37
 - Gordon’s model 28–31
 - assumptions 28
 - exposure time estimation 29
 - flat surface 29, 30
 - stoichiometric requirement 29
 - tubular structure 30, 31
 - Kim’s model 31–34
 - assumptions 31
 - film thickness 33, 34
 - precursor flux 33
 - reemission mechanisms 33
 - sticking coefficient 229
 - sticking probability of radicals 151
 - Stober method 73
 - strain energy 17
 - structural properties, of Al₂O₃ layer 111
 - FTIR spectroscopy 112
 - TEM images 111–113
 - substrate potential 135
 - subwavelength nanostructured optics 382
 - sulforhodamine B 315
 - surface chemistry 135
 - surface diffusion 136
 - surface passivation, of crystalline Si 152, 153
 - surface properties, change of 195
 - inherent surface reactivity 203, 204
 - polymers 201–203
 - self-assembled monolayers 195–197, 199–201
 - vapor-phase deposition 204, 205
 - surface reaction 4, 6, 8, 14
 - during ABC alucone growth 89, 90
 - in ALD 14–16, 281
 - formation of Sr(OH)₂ and Ba(OH)₂ and loss of 406
 - hampered at surfaces 114
 - heats of reaction 86
 - kinetics 66
 - mechanism 90
 - during MLD with TMA and EG 89
 - rates, and processes 136
 - TMA/OH surface reaction 272
 - surface recombination probability 137
 - synthetic opals 349–352
 - GLAD techniques 350
 - IHEISA technique 352
 - Langmuir–Blodgett (LB) technique 352
 - optical structure 351
 - sedimentation process, to fabricate 351
- t**
- Ta [N(CH₃)₂]₅ precursor 147
 - tantalum films 403
 - Ta₂O₅–Al₂O₃ nanolaminate 383
 - teflon 416
 - TEM analysis. *see* transmission electron microscopy (TEM) analysis
 - tensile test curves, of silk fiber 309
 - ternary compounds, studied in ALD 414, 415
 - tetraethoxysilane (TEOS) 74
 - tetrakis(diethylamido)titanium (TDEAT) 200

- tetrakis(dimethylamido)titanium (TDMAT) 200, 319
- tetrakis(dimethylamido)zirconium (TDMAZ) 200
- tetrakis(dimethylamido) zirconium(IV) (TDMA(Zr)) 113, 200
- tetrakis(dimethylamino)hafnium [Hf(NMe₂)₄], 34
- tetrakis(ethylmethylamino)hafnium (TEMAH) 34, 35
- tetramethylaluminum (TMA) 203
- –Si(CH₃)₂–O–linkage 100
- thermal ALD processes 146
- thickness evolution, of Pt and PtO₂ films 148
- thickness profile, of TiO₂ film 37
- thin film electroluminescent (TFEL) 358, 378
- thin film encapsulation 383–385
- thin film gas diffusion barriers 117–119
- three-dimensional photonic band structures 349
- through-silicon via (TSV) technology 162
- TiN ALD layer nucleation 275
- TiO₂
- Al₂O₃ nanolaminates 380
 - nucleation 280
 - photocatalytic effect 260
- TiO₂ nanoparticles. *see also* nanoparticles
- applications 251
- TiO₂/NiO ALD nanolaminates 380
- Ti–O–Ti bond formation 75
- TiO₂/ZnO nanolaminates 380
- Ti precursors 145, 200, 202, 280
- titania/alumina ALD nanolaminates 380
- titania deposition, from Ti(OiPr)₄ 69
- titania nanoparticles, for ALD 69
- titanicene MLD films 86
- titanium isopropoxide (TIP) 202, 279
- titanium oxide (TiO₂) 123, 354
- titanium tetrachloride (TiCl₄) precursor 201
- titanium tetraisopropoxide 36, 302
- thickness profile of TiO₂ film 37
- titanium tetraisopropyl oxide 113
- titanium tetramide (Ti(NH₂)₄) 200
- TMA 285, 287
- chemisorption 236
 - exposure 238
 - injection time 36
 - water ALD processes 272
 - water cycles 272
- tobacco mosaic virus, ALD on 283
- transition states (TS) 5
- calculation of 10–12
 - first-order saddle points on system PES 10
- transmission electron microscopy (TEM) 111, 112, 230, 282
- ALD Al₂O₃-coated ZnO nanorods 262
 - Al₂O₃ ALD
 - – on ethanol-dispersed SWCNT bundles 334
 - – onto polyvinyl alcohol fibers 288
 - Al₂O₃-coated SWCNT 332
 - Al₂O₃-TiO₂ nanolaminate with 17 alternating sublayers 388
 - alumina-coated titania nanoparticles 252
 - broken storage node 165
 - carbon aerogel 243
 - CNTs coated with V₂O₄ 336
 - Cu nanoparticle chains 259
 - neat Al₂O₃ layer 112
 - nonreactive polypropylene fiber 275
 - NO₂/TMA functionalized MWCNTs after 50 ALD cycles 335
 - nylon 6 fibers 290
 - one branched tube of MgAl₂O₄ 266
 - one MgO–MgAl₂O₄ core–shell nanowire 266
 - one Zn₂SiO₄ nanotube with Au nanocrystallites 264
 - of polypropylene 287
 - polypropylene after coating using TMA/water 287
 - of self-assembled organic multilayer/TiO₂ nanolaminate films 385
 - smooth surface texture 288
 - TMV treated with TiO₂ by ALD 303
 - untreated MWCNTs after 50 ALD cycles of Al₂O₃ 335
 - ZnAl₂O₄ nanotubes 262
 - ZnO nanowires shelled by TiO₂ layer 263
 - ZnO–TiO₂ core–shell nanowires 260
- transmission electron microscopy (TEM) analysis 278
- transparent conductive oxides (TCOs) 306, 317
- tridecafluoro-1,1,2,2-tetrahydrooctyltrichlorosilane (FOTS) 204
- triethylenediamine (TED) 103
- trilayer NWs 264
- trimethylaluminum (TMA) 14, 16, 18, 34, 66, 85, 86, 88, 91–93, 97, 99, 101, 105, 199, 203, 229, 237, 239, 272, 276, 277, 281, 285, 287, 288, 290, 291, 302, 331, 332, 337, 407, 416
- tris(8-hydroxyquinolino)aluminum (Alq₃) 277

tris(8-hydroxyquinoline) gallium (GaQ₃)
 nanowires 283
 tunable PC structures 366–369

u

ultrahigh vacuum (UHV) environment 72
 ultrathin hybrid nanolaminates 385
 UV-induced wetting transitions 276
 UV radiation, in plasmas 152

v

vacuum ultraviolet (VUV) radiation 152, 153
 vanadium oxide–CNT composite 329
 van der Waals forces 352
 van der Waals interactions 195, 305, 328
 vapor deposition techniques 271
 vapor-phase atomic layer deposition 272
 vibrational partition functions 10

w

wafer level 162, 179, 180
 W/Al₂O₃ layers 380
 water vapor transmission rates (WVTRs) 117,
 118, 124, 276, 277
 – vs. Al₂O₃/ZrO₂ nanolaminate
 thickness 117
 water window 380
 wave function-based quantum simulations 5,
 6
 wave function methods 5–8

x

X-ray diffraction theory 346
 – Bragg peak 346, 347
 X-ray photoelectron spectroscopy (XPS) 76,
 102, 288, 411, 412
 X-ray reflectivity (XRR)
 – analysis of TMA + GL MLD films 96
 – for characterization of ultrathin
 materials 381
 – scan of an ABC MLD film 99
 – spectra of nanolaminates of alternating
 W/Al₂O₃ layers 380

y

Yablonovite structure 350
 yttrium-stabilized zirconia (YSZ)
 – for fuel cell applications 207
 – to reduce thickness of electrolyte 393
 – selective deposition of Pt films on 215
 – small grain sizes 393

z

zero-point energies 10
 zincone MLD films 86
 zinc selenide 378
 zinc sulfide (ZnS : Mn) films
 358, 378
 zirconium tetramide (Zr(NH₂)₄) 200
 zirconium tetrat-butoxide 86
 ZnAl mixed metal oxide (MMO)
 framework 315
 ZnO ALD cycles
 – for quantum dot film 231
 – SEM images of silica aerogel vs. ZnO ALD
 cycles 241
 – vs. mass gain and Zn EDAX signal,
 on silica aerogel 241
 ZnO ALD films 103, 104, 235
 ZnO–Au–Al₂O₃ system 265
 ZnO-coated collagen 280
 ZnO-coated porous alumina 318
 ZnO film coverage 34
 ZnO, for transparent conducting
 electrodes 216
 ZnO inverse opals, optical
 properties 360
 ZnO nanolaminates 380
 ZnO nanoparticles 266, 331
 ZnO NW surface 258, 260
 ZnO oxide semiconductor
 channel layer 177
 ZnO–SiO₂, reaction 264
 Zn-porphyrin 310
 Zn₂SiO₄ nanotube 264
 ZrO₂ films 417
 Zr precursor 113, 200

